

MPS2907A TRANSISTOR (PNP)

FEATURES

Power dissipation

$$P_{CM}: 0.625 \text{ W (Tamb=25}^\circ\text{C)}$$

Collector current

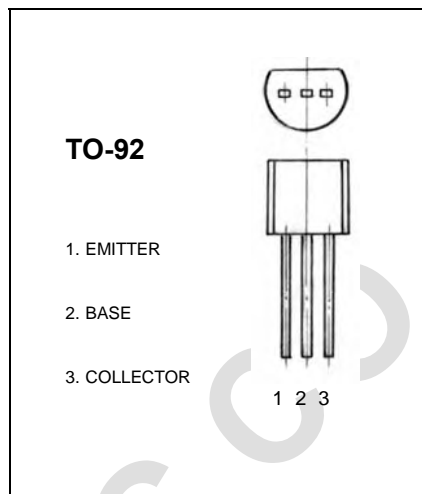
$$I_{CM}: -0.6 \text{ A}$$

Collector-base voltage

$$V_{(BR)CBO}: -60 \text{ V}$$

Operating and storage junction temperature range

$$T_J, T_{stg}: -55^\circ\text{C to } +150^\circ\text{C}$$



ELECTRICAL CHARACTERISTICS (Tamb=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -10\mu\text{A}, I_E = 0$	-60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -10\text{mA}, I_B = 0$	-60			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -10\mu\text{A}, I_C = 0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB} = -50\text{V}, I_E = 0$			-0.01	μA
Collector cut-off current	I_{CEO}	$V_{CE} = -35\text{V}, I_B = 0$			-0.05	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -3\text{V}, I_C = 0$			-0.01	μA
DC current gain	h_{FE}	$V_{CE} = -10\text{V}, I_C = -150\text{mA}$	100		300	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -500\text{mA}, I_B = -50\text{mA}$			-0.6	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -500\text{mA}, I_B = -50\text{mA}$			-1.2	V
Transition frequency	f_T	$V_{CE} = -20\text{V}, I_C = -50\text{mA}$ $f = 100\text{MHz}$	200			MHz

CLASSIFICATION OF $h_{FE(1)}$

Rank	L	H
Range	100-200	200-300